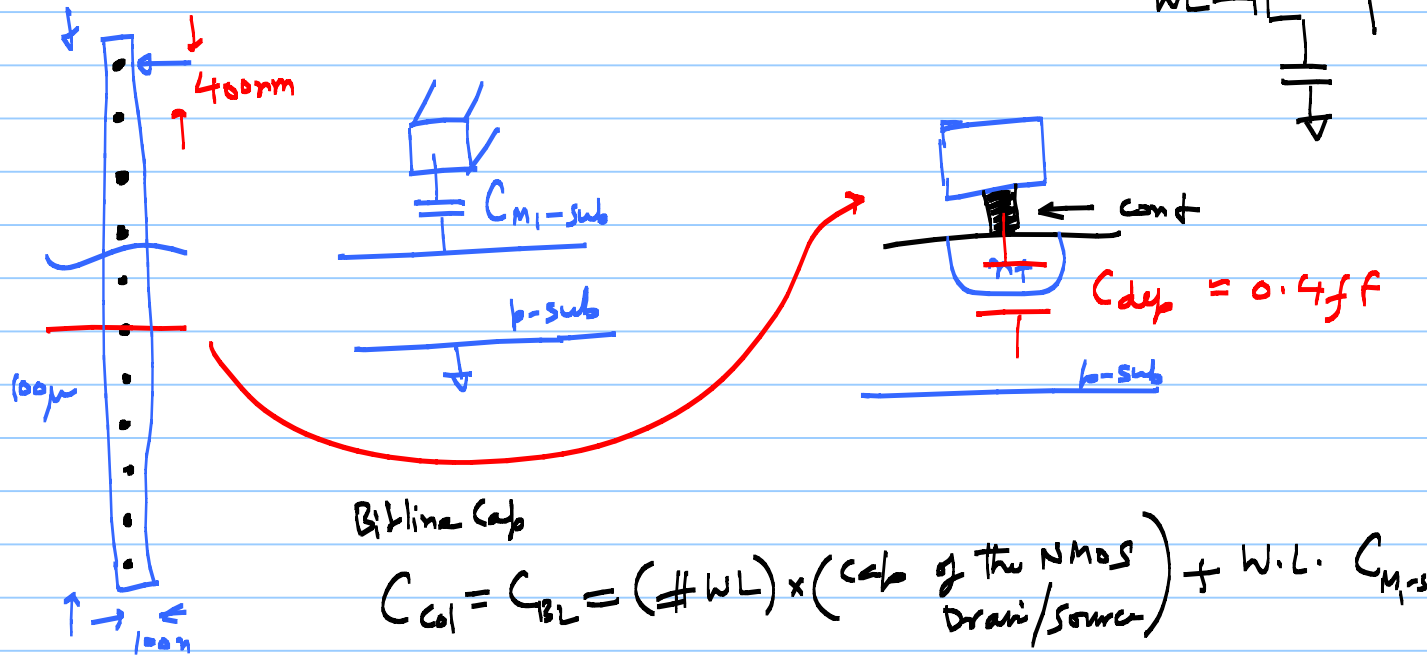


ECE 518 - Lecture 2

Note Title

1/24/2013



Bilinear Cap

$$C_{col} = C_{BL} = (\#WL) \times (\text{cap of the NMOS Drain/Source}) + W \cdot L \cdot C_{M1-sub}$$

$$\#WL = 250$$

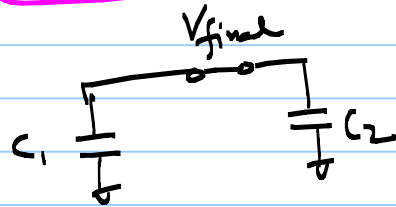
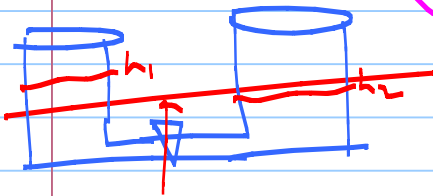
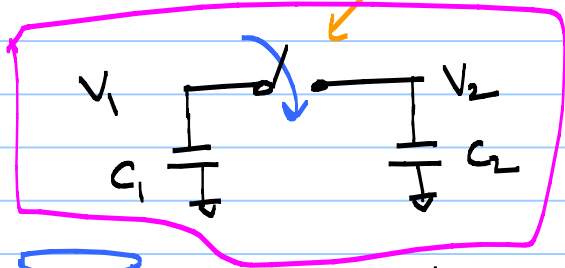
$$= 250 \times 0.4f + \frac{0.1}{\mu m} \times \frac{100}{\mu m} \times \frac{100aF}{\mu m^2}$$

$$= 100f + 1f$$

$$\approx \boxed{100fF}$$

charge-sharing

NMOS

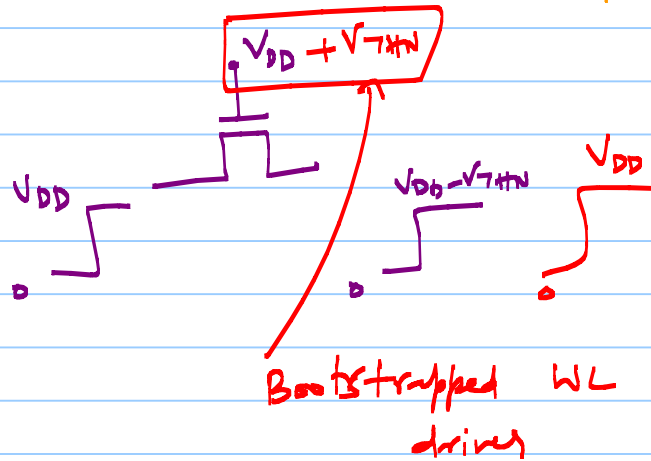


$$Q_i = Q_f$$

$$C_1 V_1 + C_2 V_2 = (C_1 + C_2) V_{final}$$

$$V_{final} = \frac{C_1 V_1 + C_2 V_2}{C_1 + C_2}$$

weighted average



$$V_1 = V_{DD} = 1V$$

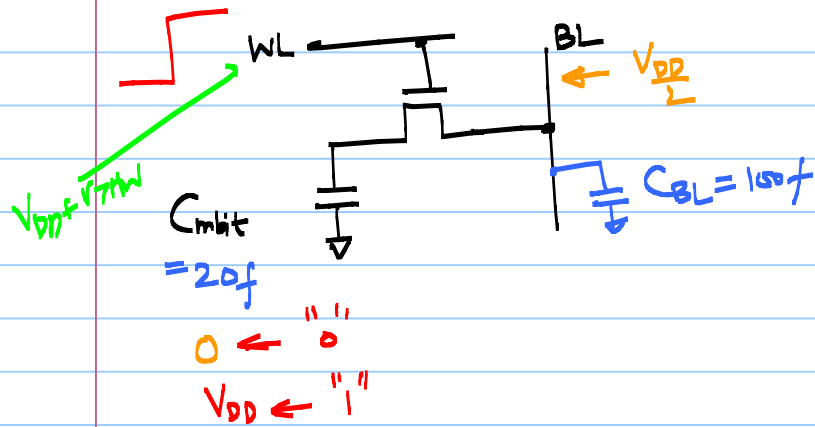
$$V_L = 0V$$

$$V_{final} = \left(\frac{C_1}{C_1 + C_L} \right) V_{DD}$$

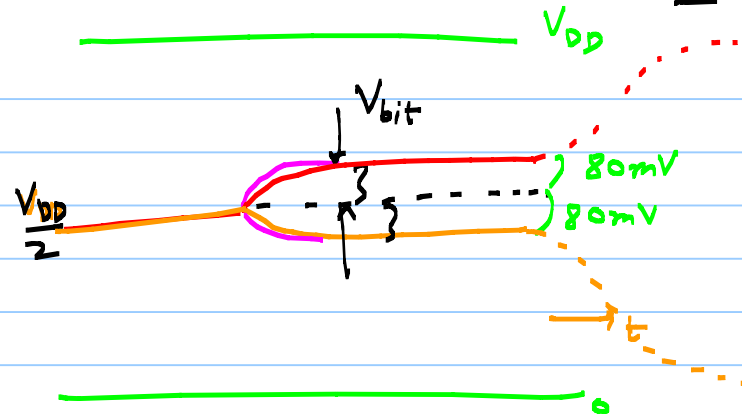
$$\text{for } C_1 = \frac{C_2}{9} = \frac{1}{10} \cdot V_{DD} = 0.1V$$

Sensing :

1T1C DRAM Cell

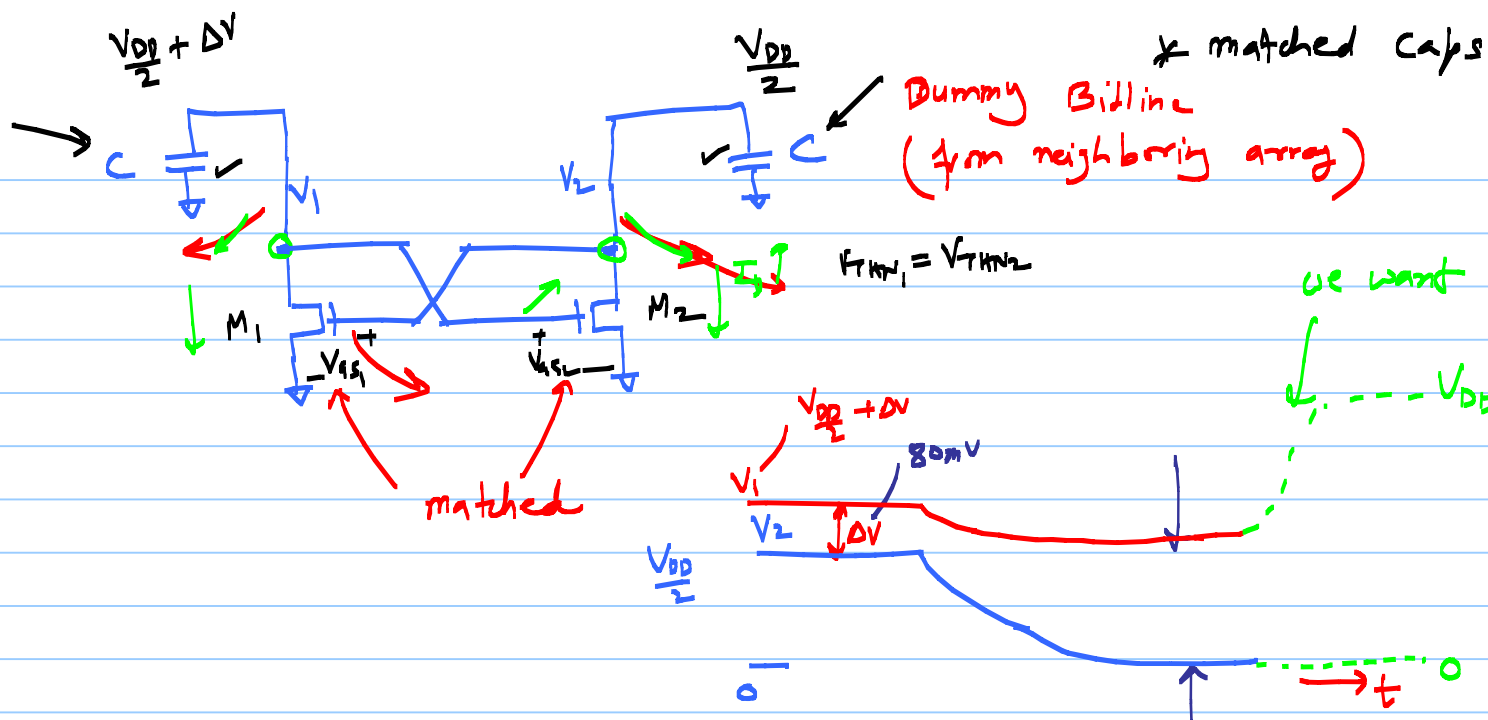


We precharge BL's to $\frac{V_{DD}}{2}$



* Need a sense amp to further drive BL's to full rails

CBL



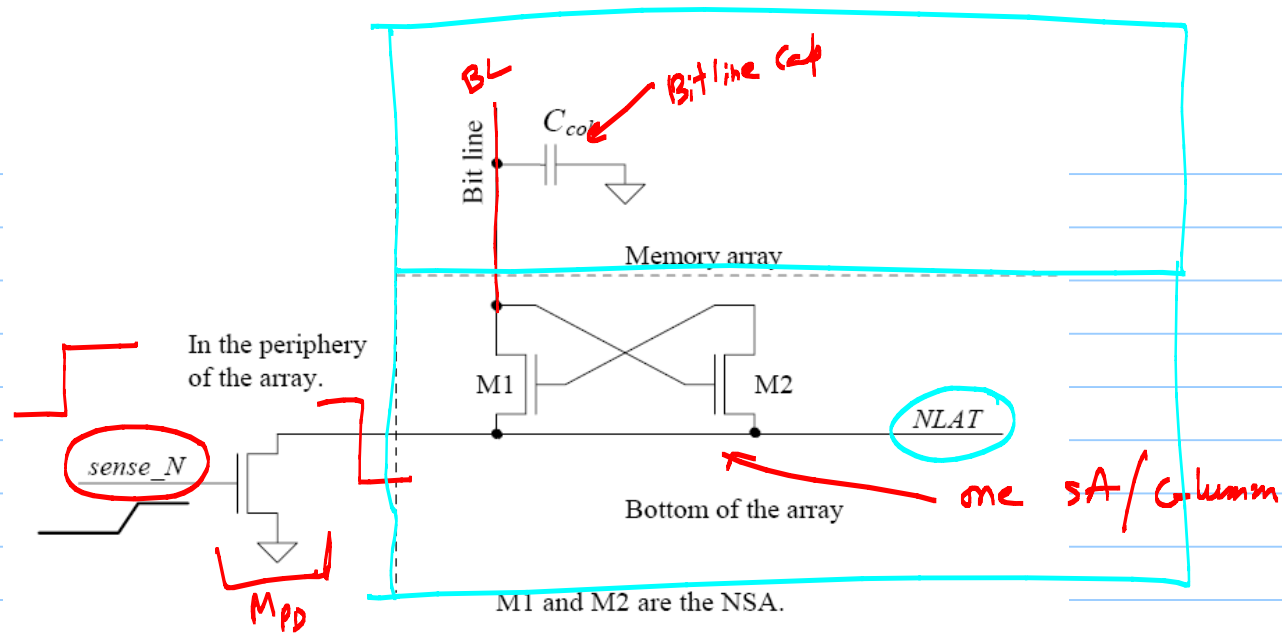
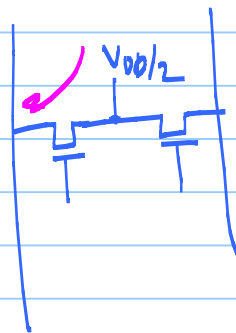
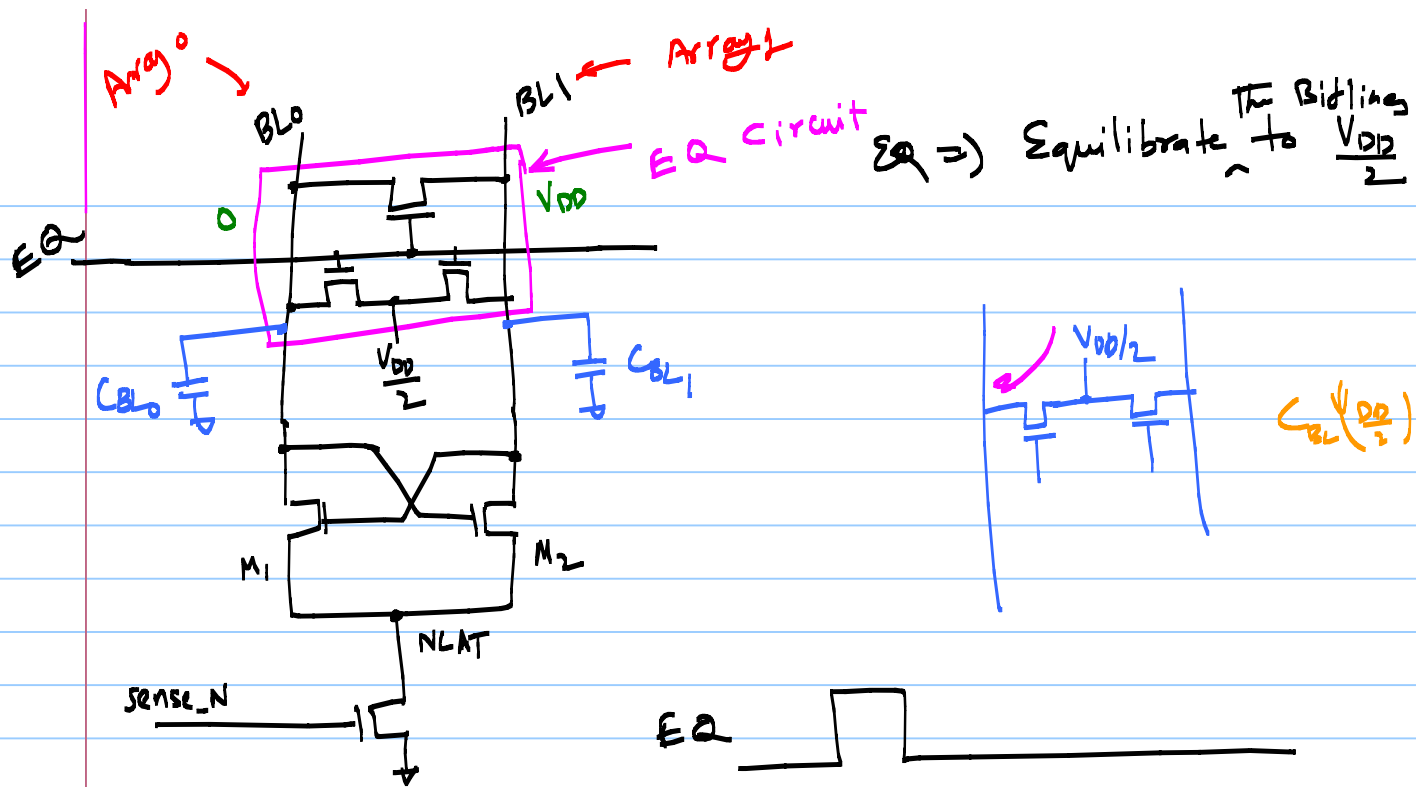
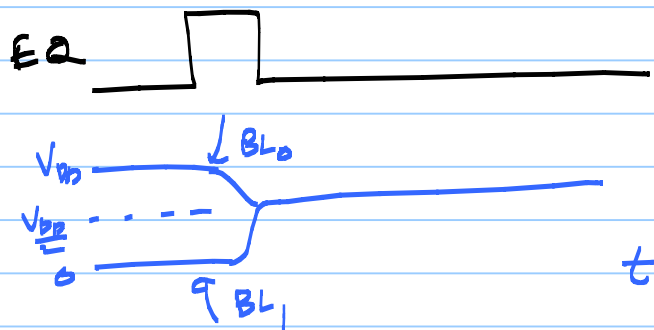


Figure 16.5 Development of an NMOS sense amplifier (NSA).



$$C_{BL} \left(\frac{V_{DD}}{2} \right)^2 f$$



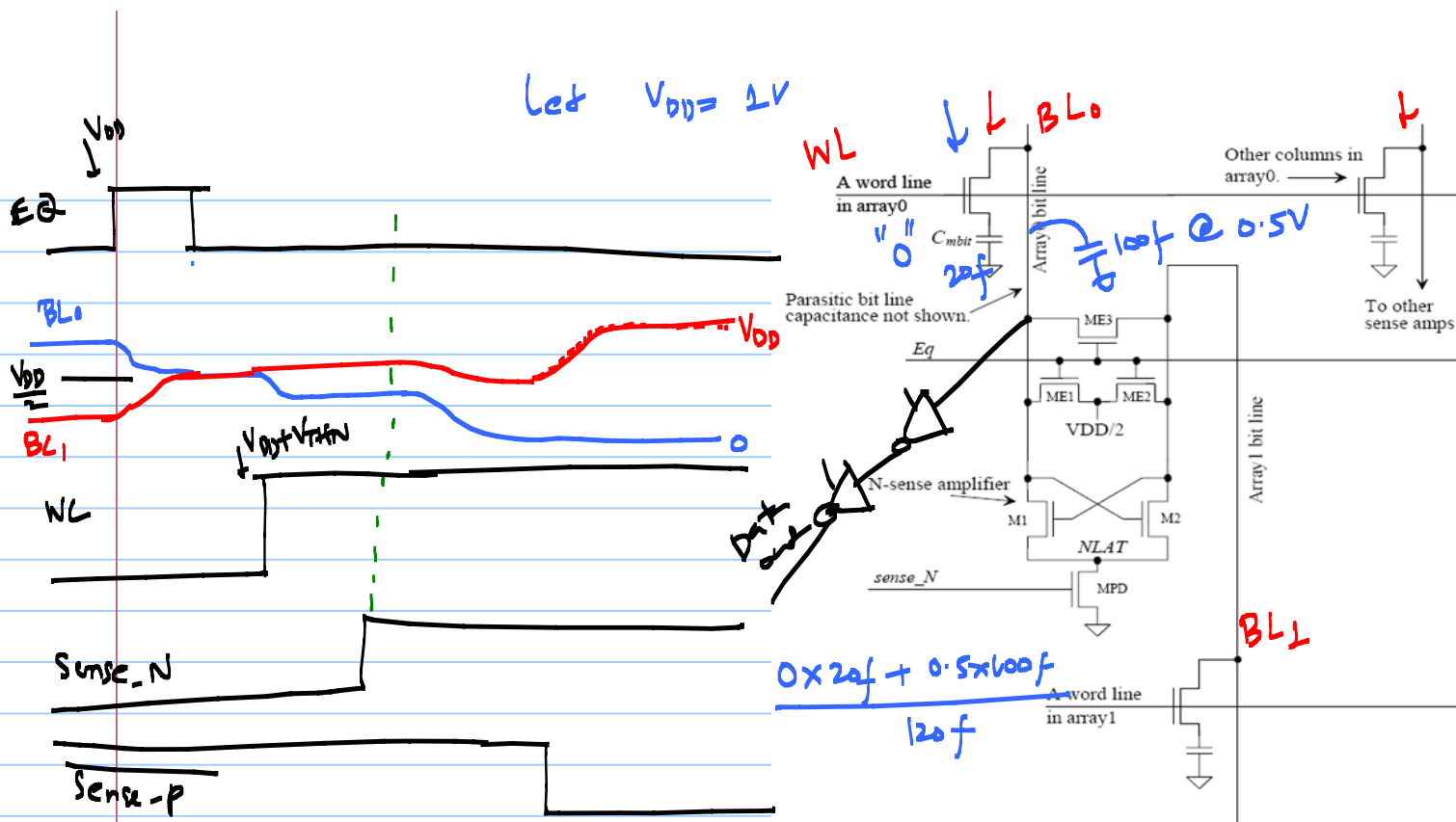


Figure 16.10 The connection of the NSA to the memory arrays.

$$C_{\text{mbit}} \leftarrow 0, V_{\text{DD}} \leftarrow V_{\text{mbit}}$$

$$C_{\text{BL}} \leftarrow \frac{V_{\text{DD}}}{2}$$

After charge sharing

$$V_{\text{final}} = \frac{C_{\text{mbit}} \cdot V_{\text{mbit}} + C_{\text{BL}} \cdot \frac{V_{\text{DD}}}{2}}{C_{\text{mbit}} + C_{\text{BL}}}$$

$$\Delta V_{\text{BL}} = V_{\text{final}} - \frac{V_{\text{DD}}}{2} = \frac{C_{\text{mbit}}}{C_{\text{mbit}} + C_{\text{BL}}} \left(V_{\text{mbit}} - \frac{V_{\text{DD}}}{2} \right)$$

$$= \left(\frac{C_{\text{mbit}}}{C_{\text{mbit}} + C_{\text{BL}}} \right) \cdot \frac{V_{\text{DD}}}{2}$$

$$\# \text{WL} \cdot C_{\text{avg}}$$

$$P_{avg} = (\# SA) \cdot C_{BL} \cdot \left(\frac{V_{DD}}{2}\right)^2 \cdot f_{read}$$

* Self refreshing reads

